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C10

5. (Amended) A method as claimed in claim 1, characterised in that on the gate electrode (1) an isolating layer (26) is deposited, on which a shielding electrode (27) is produced at the location of the gate electrode (1).

6. (Amended) A method as claimed in claim 1, characterised in that the spacers (5) are formed of a layer (5A) of silicon nitride.

7. (Amended) A method as claimed in claim 1, characterised in that the spacers (5) are formed of a layer of silicon nitride (5A) on which a layer (5B) of polycrystalline silicon is deposited.

8. (Amended) A method as claimed in claim 1, characterised in that additional semiconductor elements and preferably one or more passive components are integrated into the semiconductor body (10).

9. (Amended) A semiconductor device comprising a field-effect transistor obtained by means of a method as claimed in claim 1.

REMARKS

The foregoing amendments to claims 3-9, were made solely to avoid filing the claims in the multiple dependent form so as to avoid the additional filing fee.